

2N5883, 2N5884 (PNP) 2N5885, 2N5886 (NPN)

2N5884 and 2N5886 are Preferred Devices

Complementary Silicon High-Power Transistors

Complementary silicon high-power transistors are designed for general-purpose power amplifier and switching applications.

Features

- Low Collector–Emitter Saturation Voltage –
 $V_{CE(sat)} = 1.0 \text{ Vdc}$, (max) at $I_C = 15 \text{ Adc}$
- Low Leakage Current
 $I_{CEX} = 1.0 \text{ mAdc}$ (max) at Rated Voltage
- Excellent DC Current Gain –
 $h_{FE} = 20$ (min) at $I_C = 10 \text{ Adc}$
- High Current Gain Bandwidth Product –
 $f_T = 4.0 \text{ MHz}$ (min) at $I_C = 1.0 \text{ Adc}$
- Pb–Free Packages are Available*

MAXIMUM RATINGS (Note 1)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage 2N5883, 2N5885 2N5884, 2N5886	V_{CEO}	60 80	Vdc
Collector–Base Voltage 2N5883, 2N5885 2N5884, 2N5886	V_{CB}	60 80	Vdc
Emitter–Base Voltage	V_{EB}	5.0	Vdc
Collector Current – Continuous Peak	I_C	25 50	Adc
Base Current	I_B	7.5	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	200 1.15	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Case	θ_{JC}	0.875	$^\circ\text{C}/\text{W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Indicates JEDEC registered data. Units and conditions differ on some parameters and re–registration reflecting these changes has been requested. All above values most or exceed present JEDEC registered data.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



ON Semiconductor®

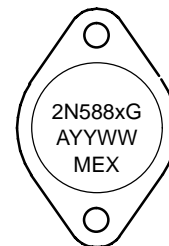
<http://onsemi.com>

25 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60 – 80 VOLTS, 200 WATTS



TO–204AA (TO–3)
CASE 1–07
STYLE 1

MARKING DIAGRAM



2N588x = Device Code
x = 3, 4, 5, or 6
G = Pb–Free Package
A = Assembly Location
YY = Year
WW = Work Week
MEX = Country of Origin

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

2N5883, 2N5884 (PNP) 2N5885, 2N5886 (NPN)

ELECTRICAL CHARACTERISTICS (Note 2) ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
Collector–Emitter Sustaining Voltage (Note 3) ($I_C = 200\text{ mA}$, $I_B = 0$)	2N5883, 2N5885 2N5884, 2N5886	$V_{CE(sus)}$	60 80	– –	Vdc
Collector Cutoff Current ($V_{CE} = 30\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 40\text{ Vdc}$, $I_B = 0$)	2N5883, 2N5885 2N5884, 2N5886	I_{CEO}	– –	2.0 2.0	mA
Collector Cutoff Current ($V_{CE} = 60\text{ Vdc}$, $V_{BE(off)} = 1.5\text{ Vdc}$) ($V_{CE} = 80\text{ Vdc}$, $V_{BE(off)} = 1.5\text{ Vdc}$) ($V_{CE} = 60\text{ Vdc}$, $V_{BE(off)} = 1.5\text{ Vdc}$, $T_C = 150^\circ\text{C}$) ($V_{CE} = 80\text{ Vdc}$, $V_{BE(off)} = 1.5\text{ Vdc}$, $T_C = 150^\circ\text{C}$)	2N5883, 2N5885 2N5884, 2N5886 2N5883, 2N5885 2N5884, 2N5886	I_{CEX}	– – – –	1.0 1.0 10 10	mA
Collector Cutoff Current ($V_{CB} = 60\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 80\text{ Vdc}$, $I_E = 0$)	2N5883, 2N5885 2N5884, 2N5886	I_{CBO}	– –	1.0 1.0	mA
Emitter Cutoff Current ($V_{EB} = 5.0\text{ Vdc}$, $I_C = 0$)		I_{EBO}	–	1.0	mA

ON CHARACTERISTICS

DC Current Gain (Note 3) ($I_C = 3.0\text{ A}$, $V_{CE} = 4.0\text{ Vdc}$) ($I_C = 10\text{ A}$, $V_{CE} = 4.0\text{ Vdc}$) ($I_C = 25\text{ A}$, $V_{CE} = 4.0\text{ Vdc}$)	h_{FE}	35 20 4.0	– 100	–
Collector–Emitter Saturation Voltage (Note 3) ($I_C = 15\text{ A}$, $I_B = 1.5\text{ A}$) ($I_C = 25\text{ A}$, $I_B = 6.25\text{ A}$)	$V_{CE(sat)}$	– –	1.0 4.0	Vdc
Base–Emitter Saturation Voltage (Note 3) ($I_C = 25\text{ A}$, $I_B = 6.25\text{ A}$)	$V_{BE(sat)}$	–	2.5	Vdc
Base–Emitter On Voltage (Note 3) ($I_C = 10\text{ A}$, $V_{CE} = 4.0\text{ Vdc}$)	$V_{BE(on)}$	–	1.5	Vdc

DYNAMIC CHARACTERISTICS

Current–Gain – Bandwidth Product (Note 4) ($I_C = 1.0\text{ A}$, $V_{CE} = 10\text{ Vdc}$, $f_{test} = 1.0\text{ MHz}$)	f_T	4.0	–	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{ob}	– –	1000 500	pF
Small–Signal Current Gain ($I_C = 3.0\text{ A}$, $V_{CE} = 4.0\text{ Vdc}$, $f_{test} = 1.0\text{ kHz}$)	h_{fe}	20	–	–

SWITCHING CHARACTERISTICS

Rise Time	$(V_{CC} = 30\text{ Vdc}, I_C = 10\text{ A}, I_{B1} = I_{B2} = 1.0\text{ A})$	t_r	–	0.7	μs
Storage Time		t_s	–	1.0	μs
Fall Time		t_f	–	0.8	μs

2. Indicates JEDEC Registered Data.

3. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

4. $f_T = |h_{fe}| \cdot f_{test}$.

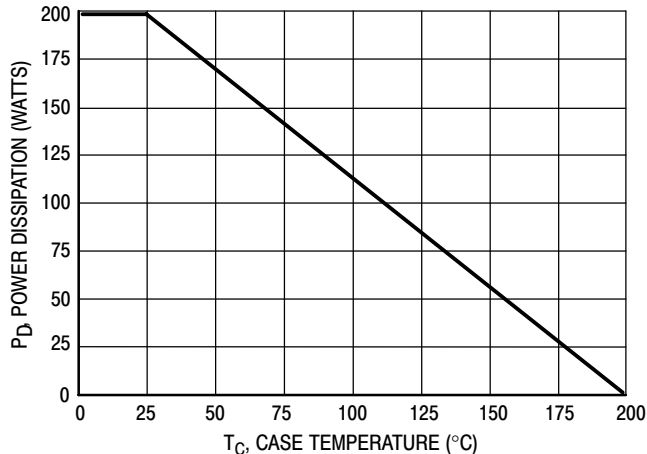


Figure 1. Power Derating

2N5883, 2N5884 (PNP) 2N5885, 2N5886 (NPN)



FOR CURVES OF FIGURES 3 & 6, R_B & R_L ARE VARIED.
 INPUT LEVELS ARE APPROXIMATELY AS SHOWN.
 FOR NPN, REVERSE ALL POLARITIES.

Figure 2. Switching Time Equivalent Test Circuits



Figure 3. Turn-On Time

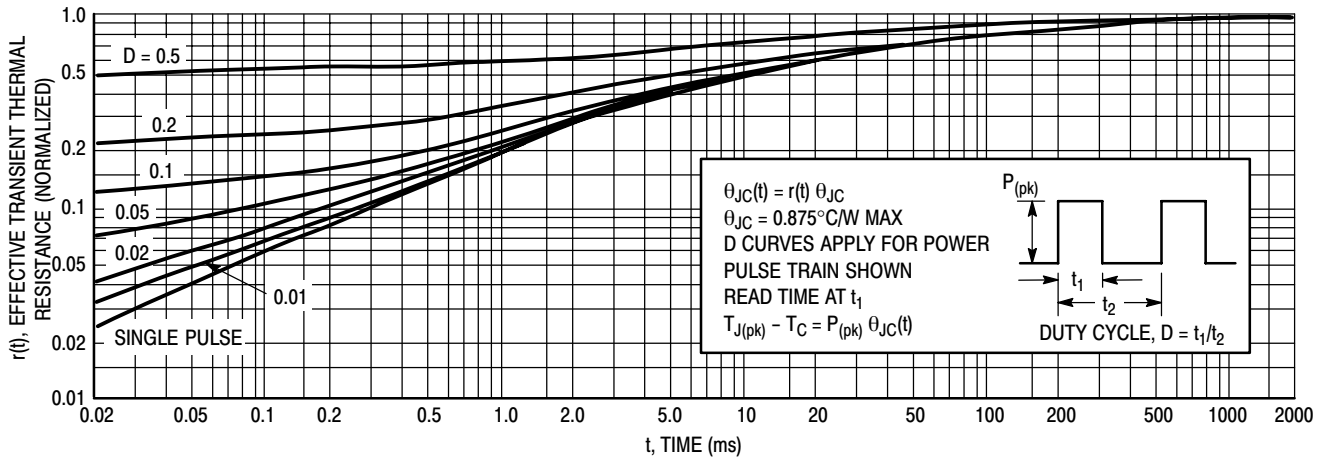


Figure 4. Thermal Response



Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 200^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 200^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

2N5883, 2N5884 (PNP) 2N5885, 2N5886 (NPN)

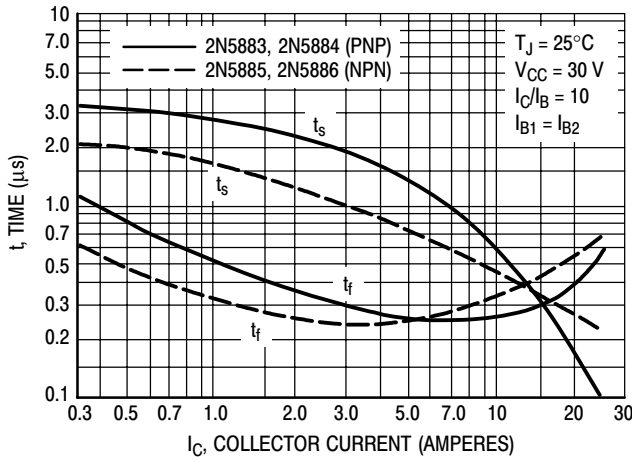


Figure 6. Turn-Off Time

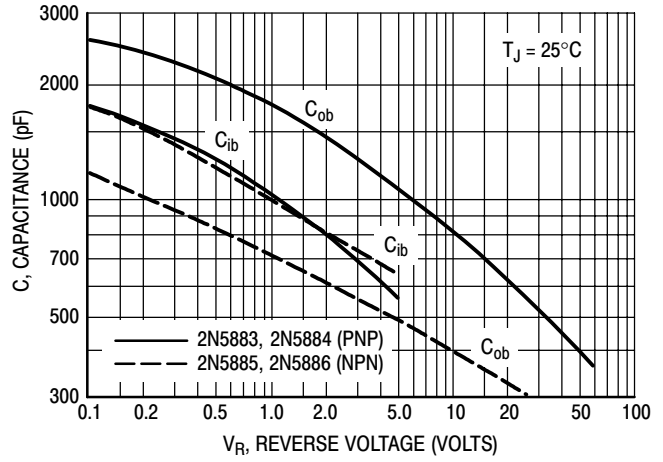


Figure 7. Capacitance

PNP DEVICES
2N5883 and 2N5884



Figure 8. DC Current Gain

NPN DEVICES
2N5885 and 2N5886

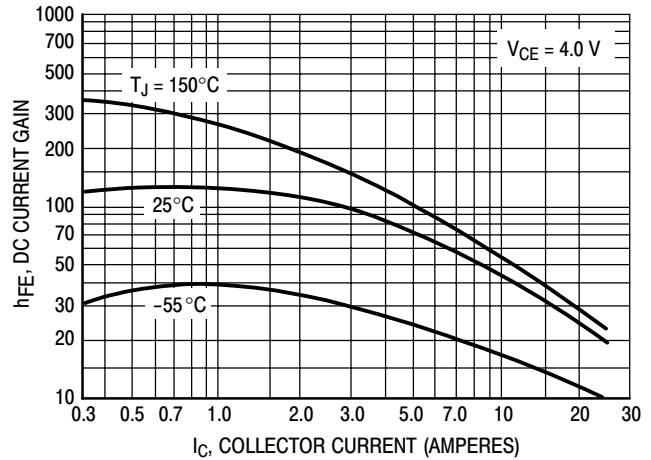


Figure 9. DC Current Gain



Figure 10. Collector Saturation Region

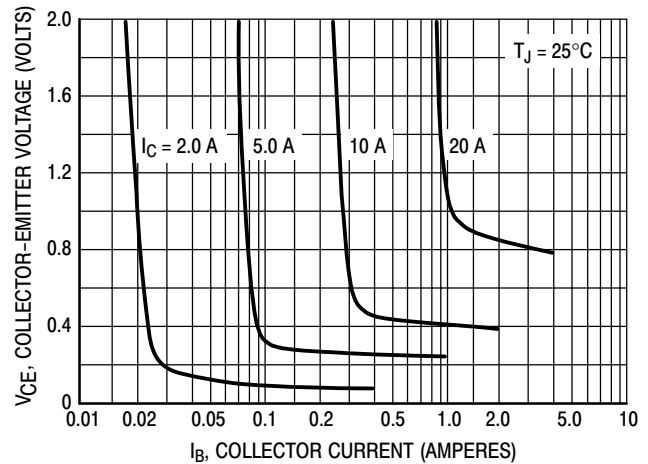


Figure 11. Collector Saturation Region

2N5883, 2N5884 (PNP) 2N5885, 2N5886 (NPN)



Figure 12. "On" Voltages



Figure 13. "On" Voltages

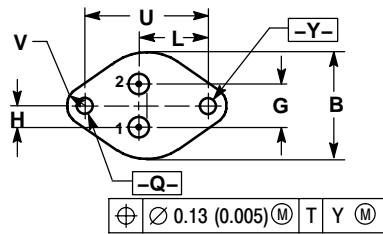
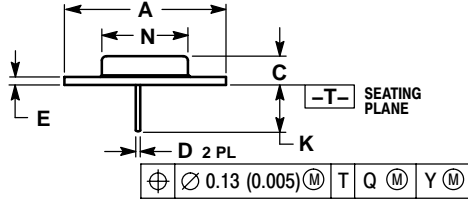
ORDERING INFORMATION

Device	Package	Shipping
2N5883	TO-204	100 Units / Tray
2N5883G	TO-204 (Pb-Free)	
2N5884	TO-204	
2N5884G	TO-204 (Pb-Free)	
2N5885	TO-204	
2N5885G	TO-204 (Pb-Free)	
2N5886	TO-204	
2N5886G	TO-204 (Pb-Free)	

2N5883, 2N5884 (PNP) 2N5885, 2N5886 (NPN)

PACKAGE DIMENSIONS

TO-204 (TO-3) CASE 1-07 ISSUE Z



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.550 REF		39.37 REF	
B	---	1.050	---	26.67
C	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
E	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
H	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N	---	0.830	---	21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
V	0.131	0.188	3.33	4.77

- STYLE 1:
PIN 1: BASE
2: EMITTER
CASE: COLLECTOR

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082-1312 USA
Phone: 480-829-7710 or 800-344-3860 Toll Free USA/Canada
Fax: 480-829-7709 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051
Phone: 81-3-5773-3850

ON Semiconductor Website: <http://onsemi.com>

Order Literature: <http://www.onsemi.com/litorder>

For additional information, please contact your local Sales Representative.

Компания «Life Electronics» занимается поставками электронных компонентов импортного и отечественного производства от производителей и со складов крупных дистрибьюторов Европы, Америки и Азии.

С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибьюторских договоров

Мы предлагаем:

- Конкуренеспособные цены и скидки постоянным клиентам.
- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

В составе нашей компании организован Конструкторский отдел, призванный помогать разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



Тел: +7 (812) 336 43 04 (многоканальный)

Email: org@lifeelectronics.ru